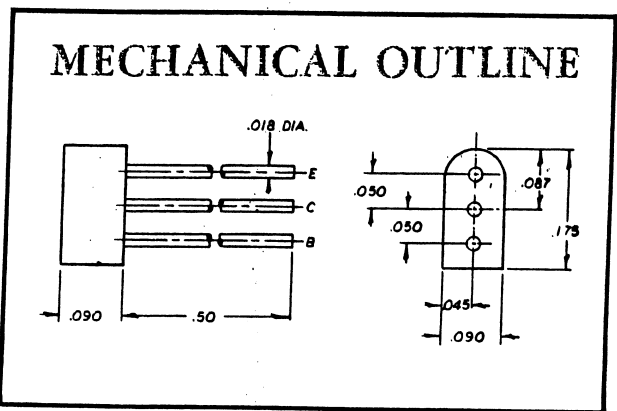


<h1 style="font-size: 2em; margin: 0;">2N4291</h1>	<h1 style="font-size: 2em; margin: 0;">Silicon PNP Transistor GEM</h1>
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APPLICATIONS

This transistor is designed for small signal general purpose applications where the low leakage currents and inherent stability of silicon devices are required.



MAXIMUM RATINGS

Total Device Dissipation - 25°C Free Air Operating and/or Storage Temperature	250mW -55 to +150°C
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DESIGN CHARACTERISTICS AT 25°C (Except as Noted)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN.	MAX.	UNITS
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100μA, I _E = 0	-40	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	-30	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100μA, I _C = 0	-6	-	V
I _{CBO}	Collector Leakage Current	V _{CB} = -15V	-	0.2	μA
h _{FE}	Forward Current Transfer Ratio	V _{CE} = -10V, I _C = 0.1mA	30	-	-
		I _C = 10mA	50	-	-
		I _C = 100mA	100	300	-
V _{CE(sat)}	Collector Saturation Voltage	I _C = 100mA, I _B = 10mA	-	-0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 100mA, I _B = 10mA	-	-1.5	V
C _{ob}	Output Capacitance	V _{CB} = -10V, f = 140kc	-	10	pf
h _{fe}	High Frequency Current Gain	I _C = 10mA, V _{CE} = -10V, f = 100mc	1.0	-	-

